SILICON NPN EPITAXIAL PLANAR TYPE

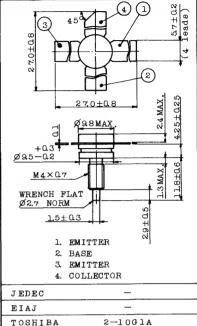
VHF BAND POWER AMPLIFIER APPLICATIONS.

FEATURES :

- . Output Power : $P_0=32W$ (Min.) $(f=175MHz, Vcc=13.5V, P_i=4W)$
- 100% Tested for Load Mismatch Stress at All Phase Angles with 30:1 VSWR @ V_{CC}=14.5V, P₁=4W, f=175MHz

MAXIMUM RATINGS ($Ta=25^{\circ}C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V _{CBO}	40	V
Collector-Emitter Voltage	VCEO	18	v
Emitter-Base Voltage	V _{EBO}	4	v
Collector Current	IC	6	А
Collector Power Dissipation (Tc=25°C)	PC	7.0	W
Junction Temperature	Tj	175	°C
Storage Temperature Range	T _{stg}	- 65~175	°C



2SC2420

ELECTRICAL CHARACTERISTICS (Tc=25°C)

Series Equivalent Output

Impedance

MTN. TYP. MAX. UNIT CHARACTERISTIC SYMBOL TEST CONDITION V_{CB}=15V, I_E=0 _ 2 Collector Cut-off Current _ mΑ ICB0 Collector-Base Breakdown v 40 V(BR)CBO $I_C=10mA$, $I_E=0$ _ **Voltage** Collector-Emitter Breakdown 18 v V(BR)CEO $I_C=25mA$, $I_B=0$ Voltage Emitter-Base Breakdown $I_E=1mA$, $I_C=0$ 4 _ v V(BR)EBO Voltage $V_{CE}=5V$, $I_C=5A$ 10 DC Current Gain h_{FE} _ _ _ 110 160 pF Соъ V_{CB}=13.5V, I_E=0, f=1MHz Collector Output Capacitance Output Power Po (Fig.) 32 34 _ W V_{CC}=13.5V, f=175MHz, 9.0 9.3 _ dB Power Gain Gpe $P_i = 4W$ 60 70 % Collector Efficiency _ $\eta_{\mathbf{C}}$ 0.9 Series Equivalent Input Z_{in} Ω V_{CC}=13.5V, f=175MHz, +j1.1 Impedance

Unit in mm

Mounting Kit No. AC57 Weight : 3.3g

2.0

-j0.4

Ω

 $P_0 = 32W$

ZOUT

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Fig. Po TEST CIRCUIT

